N-Channel MOSFET Transistor TK25A60X,ITK25A60X

FEATURES

- Low drain-so
- High-speed s
- Enhancemen
- 100% avalan

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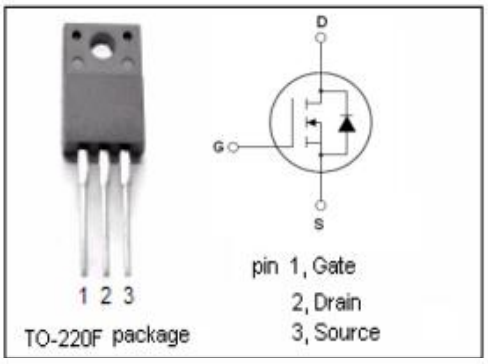

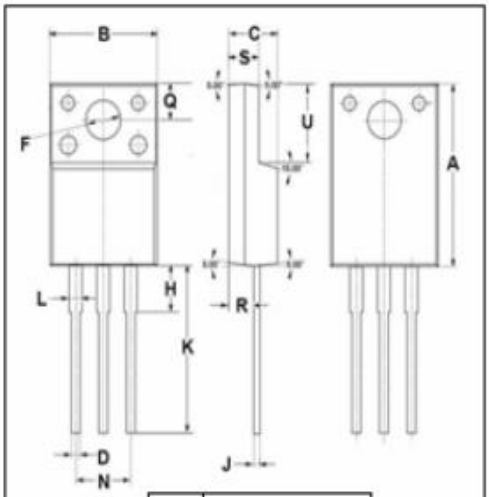

DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

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℃THERMAL CHARACTERISTICS

N-Channel MOSFET Transistor TK25A60X,ITK25A60X

ELECTRICAL CHARACTERISTICS

T_C=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 10mA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D=1.2mA	2.5		3.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=7.5A		105	125	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±30V;V_{DS}= 0V			±1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= 600V; V_{GS}= 0V			10	μA
V_{SDF}	Diode forward voltage	I_{DR} =25 A, V_{GS} = 0 V			1.7	V

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